Zheng Yang

List of Publications by Year
in descending order

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		159358	128067
67	4,684	30	60
papers	citations	h-index	g-index

67	67	67	5790
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Oxide Electronics Utilizing Ultrafast Metal-Insulator Transitions. Annual Review of Materials Research, 2011, 41, 337-367.	4.3	818
2	Ultra-thin perfect absorber employing a tunable phase change material. Applied Physics Letters, 2012, 101, .	1.5	519
3	High-mobility Sb-doped p-type ZnO by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 152101.	1.5	290
4	Electrically pumped ultraviolet ZnO diode lasers on Si. Applied Physics Letters, 2008, 93, .	1.5	267
5	Voltage-Triggered Ultrafast Phase Transition in Vanadium Dioxide Switches. IEEE Electron Device Letters, 2013, 34, 220-222.	2.2	225
6	Photoluminescence study of Sb-doped p-type ZnO films by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 252102.	1.5	197
7	Thermal tuning of mid-infrared plasmonic antenna arrays using a phase change material. Optics Letters, 2013, 38, 368.	1.7	196
8	Sb-doped p-ZnOâˆ•Ga-doped n-ZnO homojunction ultraviolet light emitting diodes. Applied Physics Letters, 2008, 92, 152103.	1.5	133
9	Work Function of Vanadium Dioxide Thin Films Across the Metal-Insulator Transition and the Role of Surface Nonstoichiometry. ACS Applied Materials & Interfaces, 2011, 3, 3396-3401.	4.0	125
10	Na-Doped p-Type ZnO Microwires. Journal of the American Chemical Society, 2010, 132, 2498-2499.	6.6	122
11	p-type behavior from Sb-doped ZnO heterojunction photodiodes. Applied Physics Letters, 2006, 88, 112108.	1.5	119
12	p-type ZnO films with solid-source phosphorus doping by molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 052106.	1.5	114
13	Dielectric and carrier transport properties of vanadium dioxide thin films across the phase transition utilizing gated capacitor devices. Physical Review B, 2010, 82, .	1.1	109
14	Homojunction photodiodes based on Sb-doped p-type ZnO for ultraviolet detection. Applied Physics Letters, 2006, 88, 092103.	1.5	98
15	Ultraviolet emission from Sb-doped p-type ZnO based heterojunction light-emitting diodes. Applied Physics Letters, 2008, 92, .	1.5	96
16	Metal-insulator transition characteristics of VO2 thin films grown on Ge(100) single crystals. Journal of Applied Physics, 2010, 108, .	1.1	95
17	Donor and acceptor competitions in phosphorus-doped ZnO. Applied Physics Letters, 2006, 88, 152116.	1.5	94
18	Research Update: Spin transfer torques in permalloy on monolayer MoS2. APL Materials, 2016, 4, .	2.2	75

#	Article	IF	Citations
19	Ultraviolet photoconductive detectors based on Ga-doped ZnO films grown by molecular-beam epitaxy. Solid-State Electronics, 2007, 51, 1014-1017.	0.8	70
20	Studies on electric triggering of the metal-insulator transition in VO2 thin films between 77 K and 300 K. Journal of Applied Physics, 2011, 110, .	1.1	62
21	Reconfigurable Vanadium Dioxide Nanomembranes and Microtubes with Controllable Phase Transition Temperatures. Nano Letters, 2018, 18, 3017-3023.	4.5	62
22	ZnO growth on Si with low-temperature ZnO buffer layers by ECR-assisted MBE. Journal of Crystal Growth, 2006, 286, 61-65.	0.7	57
23	Studies on room-temperature electric-field effect in ionic-liquid gated VO2 three-terminal devices. Journal of Applied Physics, 2012, 111, 014506.	1.1	53
24	A perspective of recent progress in ZnO diluted magnetic semiconductors. Applied Physics A: Materials Science and Processing, 2013, 112, 241-254.	1.1	50
25	Electron concentration dependent magnetization and magnetic anisotropy in ZnO:Mn thin films. Applied Physics Letters, 2008, 92, 042111.	1.5	47
26	Dominant ultraviolet light emissions in packed ZnO columnar homojunction diodes. Applied Physics Letters, 2008, 93, .	1.5	44
27	Ga-related photoluminescence lines in Ga-doped ZnO grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2009, 94, .	1.5	43
28	Bi-induced acceptor states in ZnO by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 052103.	1.5	33
29	Electron carrier concentration dependent magnetization and transport properties in ZnO:Co diluted magnetic semiconductor thin films. Journal of Applied Physics, 2008, 104, .	1.1	32
30	Al/Ti contacts to Sb-doped p-type ZnO. Journal of Applied Physics, 2007, 102, 023716.	1.1	31
31	Influence of electron injection on the photoresponse of ZnO homojunction diodes. Applied Physics Letters, 2006, 89, 142114.	1.5	29
32	Epitaxial Mn-doped ZnO diluted magnetic semiconductor thin films grown by plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2011, 314, 97-103.	0.7	29
33	Low-resistivity Auâ^•Ni Ohmic contacts to Sb-doped p-type ZnO. Applied Physics Letters, 2007, 90, 252103.	1.5	27
34	Blue electroluminescence from ZnO based heterojunction diodes with CdZnO active layers. Applied Physics Letters, 2009, 95, .	1.5	25
35	Geometric confinement effects on the metal-insulator transition temperature and stress relaxation in VO2 thin films grown on silicon. Journal of Applied Physics, 2011, 109, 063512.	1.1	25
36	Thermal stability of CdZnO thin films grown by molecular-beam epitaxy. Applied Surface Science, 2010, 256, 4734-4737.	3.1	22

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37	ZnO:Sb/ZnO:Ga Light Emitting Diode onc-Plane Sapphire by Molecular Beam Epitaxy. Applied Physics Express, 2010, 3, 032101.	1.1	22
38	Breakthroughs in Photonics 2014: Phase Change Materials for Photonics. IEEE Photonics Journal, 2015, 7, 1-5.	1.0	21
39	Optical properties of Ge/Si quantum dot superlattices. Materials Letters, 2004, 58, 3765-3768.	1.3	19
40	Study of the effect of plasma power on ZnO thin films growth using electron cyclotron resonance plasma-assisted molecular-beam epitaxy. Applied Surface Science, 2008, 255, 3375-3380.	3.1	19
41	Microstructure and transport properties of ZnO:Mn diluted magnetic semiconductor thin films. Journal of Applied Physics, 2009, 105, 053708.	1.1	16
42	Direct measurement of compositional complexity-induced electronic inhomogeneity in VO2 thin films grown on gate dielectrics. Applied Physics Letters, 2011, 98, 192113.	1.5	16
43	Strain and Phonon Confinement in Self-Assembled Ge Quantum Dot Superlattices. Chinese Physics Letters, 2003, 20, 2001-2003.	1.3	14
44	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. Journal of Applied Physics, 2006, 99, 024504.	1.1	12
45	Ultraviolet light emissions in MgZnO/ZnO double heterojunction diodes by molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D10-C3D12.	0.6	11
46	Regulating Carrier Dynamics in Single Crystal Halide Perovskite via Interface Engineering and Optical Doping. Advanced Electronic Materials, 2016, 2, 1600248.	2.6	11
47	$hbox{TiSi}_{2}$ Nanocrystal Metal Oxide Semiconductor Field Effect Transistor Memory. IEEE Nanotechnology Magazine, 2011, 10, 499-505.	1.1	10
48	Synthesis of High-Quality AgSbSe₂ and AgBiSe₂ Nanocrystals with Antimony and Bismuth Silylamide Reagents. Chemistry of Materials, 2017, 29, 4597-4602.	3.2	10
49	P-type ZnO by Sb doping for PN-junction photodetectors. , 2006, , .		9
50	Temperature-dependent photoluminescence of CdZnO thin films grown by molecular-beam epitaxy. Journal of Crystal Growth, 2009, 312, 68-72.	0.7	9
51	Multi-Resistance States Through Electrically Driven Phase Transitions in $hbox{VO}_{2}/hbox{HfO}_{2}/hbox{VO}_{2}$ Heterostructures on Silicon. IEEE Electron Device Letters, 2012, 33, 101-103.	2.2	9
52	ZnO growth on Si with low-temperature CdO and ZnO buffer layers by molecular-beam epitaxy. Journal of Electronic Materials, 2006, 35, 691-694.	1.0	8
53	Influence of electron injection on the temporal response of ZnO homojunction photodiodes. Applied Physics Letters, 2007, 91, .	1.5	7
54	Donor-acceptor-pair photoluminescence in Ga-doped ZnO thin films grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D6-C3D9.	0.6	6

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55	Homobuffer thickness effect on the background electron carrier concentration of epitaxial ZnO thin films. Journal of Applied Physics, 2010, 108, 066101.	1.1	5
56	Microstructural Models of Alumina Nanotubes and Anodic Porous Alumina Film Formed in Sulphuric Acid. Chinese Physics Letters, 2002, 19, 391-394.	1.3	4
57	Thermal annealing effect on spin coherence in ZnO single crystals. Journal of Applied Physics, 2011, 110, 016101.	1.1	4
58	Study of rapid thermal annealing effect on CdZnO thin films grown on Si substrate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D13-C3D16.	0.6	3
59	Characteristics of a phosphorus-doped p-type ZnO film by MBE. Materials Research Society Symposia Proceedings, 2005, 892, 412.	0.1	2
60	Vanadium dioxide (VO<inf>2</inf>) is also a ferroelectric: Properties from memory structures. , 2011, , .		2
61	UV photoconductors based on Ga-doped ZnO films. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	1
62	Folded Acoustic Phonon Modes in Ge/Si Quantum Dot Superlattices With Different Periods. Journal of Nanoelectronics and Optoelectronics, 2006, 1, 86-91.	0.1	1
63	Structural characteristics of self-assembled Ge/Si quantum dot superlattices. , 2004, , .		0
64	A novel approach to evaluate the carrier effective mass in GeSi quantum dot structure. , 0, , .		0
65	Electron carrier concentration dependent magnetization in ZnO:Co and ZnO:Mn thin films. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	0
66	Cyan electroluminescence from n-ZnO/i-CdZnO/p-Si heterojunction diodes. Materials Research Society Symposia Proceedings, 2009, 1201, 40.	0.1	0
67	Correlated oxide phase transition switch: A paradigm in electron devices. , 2011, , .		0